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November 2013

## **FQP22N30**

# N-Channel QFET<sup>®</sup> MOSFET 300 V, 21 A, 160 m $\Omega$

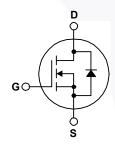
### **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### **Features**

- 21 A, 300 V,  $R_{DS(on)}$  = 160 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 10.5 A
- Low Gate Charge (Typ. 47 nC)
- Low Crss (Typ. 40 pF)
- · 100% Avalanche Tested





## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQP22N30	Unit	
$V_{DSS}$	Drain-Source Voltage		300	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		21	Α	
	- Continuous (T <sub>C</sub> = 100°C)		13.3	А	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	84	Α	
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	1000	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	21	A	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	17	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns	
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		170	W	
	- Derate above 25°C		1.35	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C	

## **Thermal Characteristics**

Symbol	Parameter	FQP22N30	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.74	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP22N30	FQP22N30	TO-220	Tube	N/A	N/A	50 units

## **Flectrical Characteristics**

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	300			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.3		V/°C
I <sub>DSS</sub>		V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V			1	μΑ
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 240 V, T <sub>C</sub> = 125°C			10	μΑ	
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10.5 A		0.12	0.16	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 10.5 A		16		S
C <sub>iss</sub>	ic Characteristics Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,		1700	2200	pF
Coss	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1.0 \text{ MHz}$		350	450	рF
C <sub>rss</sub>	Reverse Transfer Capacitance			40	50	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 150 V, I <sub>D</sub> = 22 A,		35	80	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		230	470	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			85	180	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	/	100	210	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 240 V, I <sub>D</sub> = 22 A,		47	60	nC
$Q_{gs}$	Gate-Source Charge	V <sub>GS</sub> = 10 V		12		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		24		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				21	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				84	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 21 A			1.5	V
			+	<b>-</b>	-	

## $Q_{rr}$

 $t_{rr}$ 

- Notes: Notes: Notes: A Repetitive Rating: Pulse width limited by maximum junction temperature. 
  2. L = 3.78 mH,  $I_{AS} = 21$  A,  $V_{DD} = 50$  V,  $R_G = 25$   $\Omega$ , starting  $T_J = 25^{\circ}$ C. 
  3.  $I_{SD} \le 22$  A, di/dt  $\le 200$  A/µs,  $V_{DD} \le BV_{DSS}$ , starting  $T_J = 25^{\circ}$ C. 
  4. Essentially independent of operating temperature.

Reverse Recovery Time

Reverse Recovery Charge

ns

μС

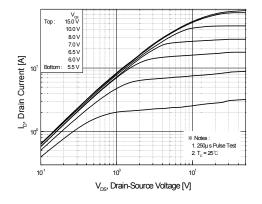
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V<sub>GS</sub> = 0 V, I<sub>S</sub> = 22 A,

 $dI_F / dt = 100 A/\mu s$ 

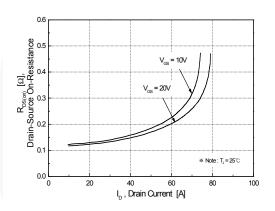
## **Typical Characteristics**



| 101 | 25°C | \*\* Notes: 1. V<sub>cs</sub> = 50V | 2.250µs Pulse Test | 101 | 26 °C | 2.250µs Pulse Test | 101 | 2.50µs Pulse Test | 102 | 2.50µs Pulse Test | 103 | 2.50µs Pulse Test | 104 | 2.50µs Pulse Test | 105 | 2.50µs Pulse Test

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



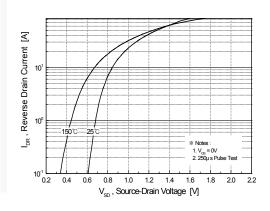
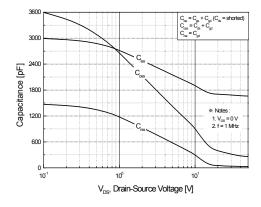


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



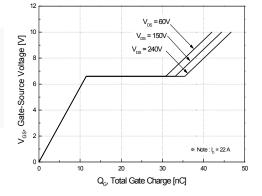
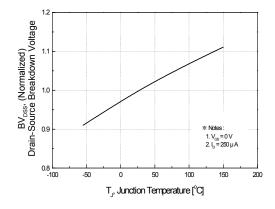


Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

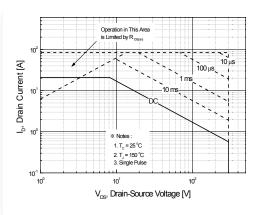
## Typical Characteristics (continued)



30 25 (Normalized) 30 25 (Solution of the properties of the proper

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



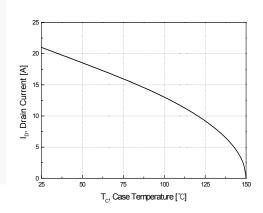


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

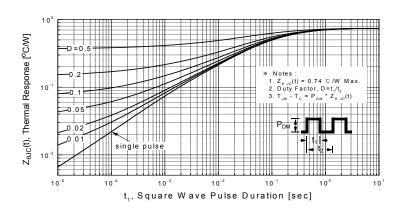


Figure 11. Transient Thermal Response Curve

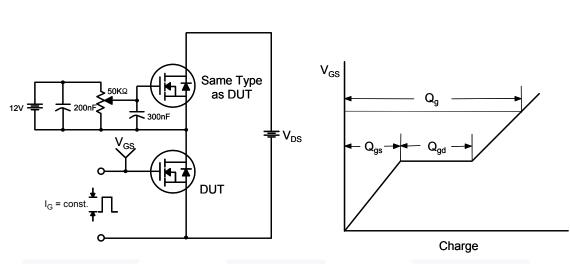


Figure 12. Gate Charge Test Circuit & Waveform

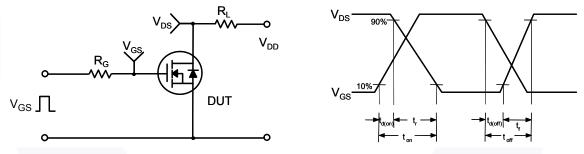


Figure 13. Resistive Switching Test Circuit & Waveforms

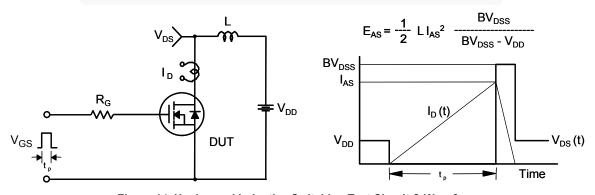
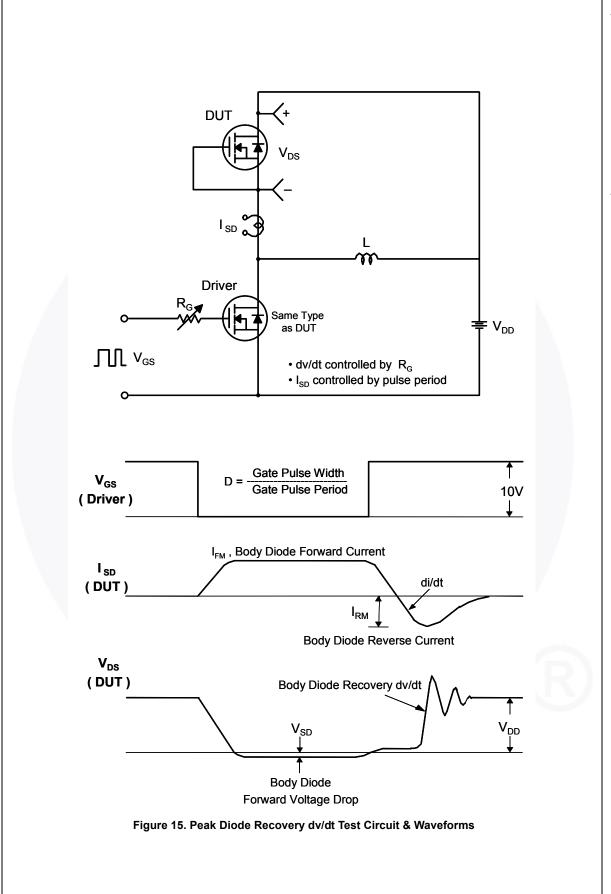
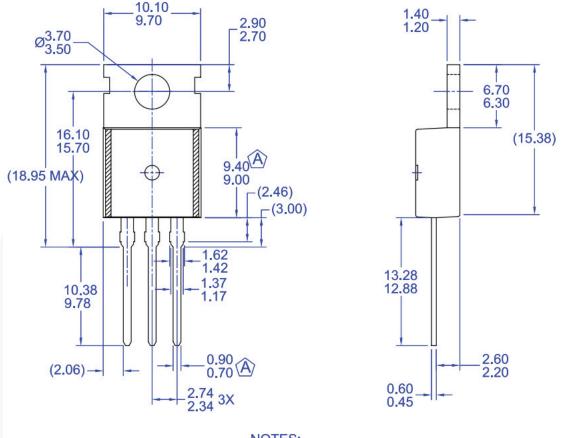


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



## **Mechanical Dimensions**



## NOTES:

- A) CONFORMS TO JEDEC TO-220

  VARIATION AB EXCEPT WHERE NOTED

  B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
  - D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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